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Telefax: +1-404-894 2866

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Higashi-Hiroshima 724, Japan
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Dept. of Metallurgy & Materials Science
Massachusetts Institute of Technology
Cambridge, MA 02139, USA
Telefax: +1-617-253 5827

**Technical Editors:** F.Y. Verploegh Chassé and J. Hanraads, Elsevier/North-Holland, P.O. Box 103, 1000 AC Amsterdam, Netherlands, Telefax: +31-20-5862 775



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# Control of Semiconductor Interfaces

Proceedings of the First International Symposium, Karuizawa, Japan, 8-12 November 1993

Edited by **I. Ohdomari**, **M. Oshima** and **A. Hiraki**

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[2] J.C. Brice, The Growth of Crystals from Liquids (North-Holland, Amsterdam, 1973) ch. 3, p. 55.
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